imall

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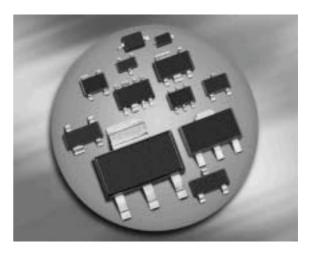




Silicon Switching Diode

- For high-speed switching applications
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101





BAL99



Туре	Package	Configuration	Marking
BAL99	SOT23	single	JFs

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V _R	80	V	
Peak reverse voltage-	V _{RM}	85		
Forward current	I _F	250	mA	
Peak forward current	/ _{FM}	-		
Surge forward current, $t = 1 \ \mu s$	IFS	4.5	A	
Total power dissipation	Ptot	370	mW	
$T_{\rm S} \le 54^{\circ}{\rm C}$				
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-65 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	≤ 260	K/W

¹Pb-containing package may be available upon special request

²For calculation of $R_{\rm thJA}$ please refer to Application Note Thermal Resistance

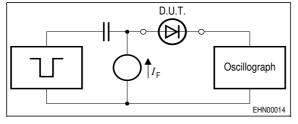


Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics		•	-		
Breakdown voltage	V _(BR)	85	-	-	V
<i>I</i> (BR) = 100 μA					
Reverse current	l _R				μA
<i>V</i> _R = 70 V		-	-	1	
$V_{\rm R} = 25 \text{ V}, \ T_{\rm A} = 150 \ ^{\circ}{\rm C}$		-	-	30	
$V_{\rm R} = 70 \text{ V}, \ T_{\rm A} = 150 \ ^{\circ}{\rm C}$		-	-	50	
Forward voltage	VF				mV
$I_{\rm F} = 1 {\rm mA}$		-	-	715	
<i>I</i> _F = 10 mA		-	-	855	
<i>I</i> _F = 50 mA		-	-	1000	
<i>I</i> _F = 150 mA		-	-	1250	
AC Characteristics					
Diode capacitance	CT	-	-	1.5	pF
$V_{R} = 0 V, f = 1 MHz$					
			-		

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

$V_{\rm R} = 0 {\rm V}, f = 1 {\rm MHz}$					
Reverse recovery time	<i>t</i> rr	-	-	4	ns
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 10 mA, measured at $I_{\rm R}$ = 1mA ,					
$R_{\rm L} = 100 \ \Omega$					

Test circuit for reverse recovery time



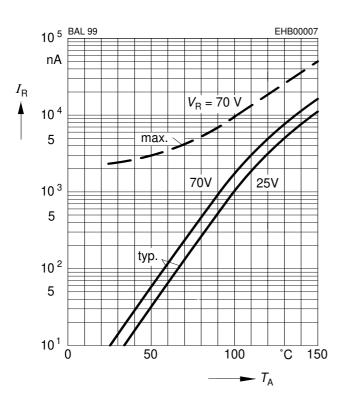
Puls generator: $t_p = 100$ ns, D = 0.05, $t_r = 0.6$ ns, $R_i = 50\Omega$ Oscillograph: R = 50, $t_r = 0.35$ ns

 $C \le 1 \text{pf}$



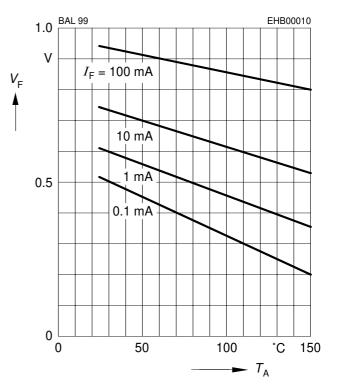
Reverse current $I_{R} = f(T_{A})$

 $V_{\rm R}$ = Parameter

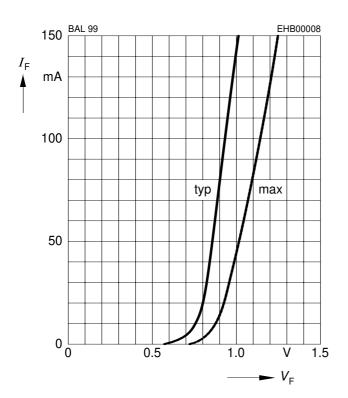


Forward Voltage $V_{F} = f(T_{A})$

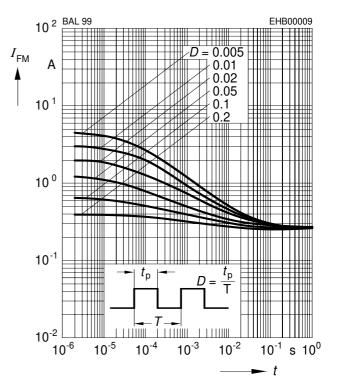
 $I_{\rm F}$ = Parameter



Forward current $I_{\rm F} = f (V_{\rm F})$

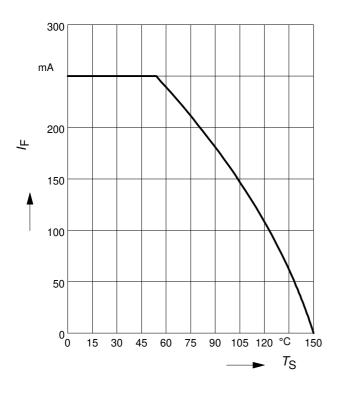


Peak forward current $I_{FM} = f(t_p)$ $T_A = 25^{\circ}C$

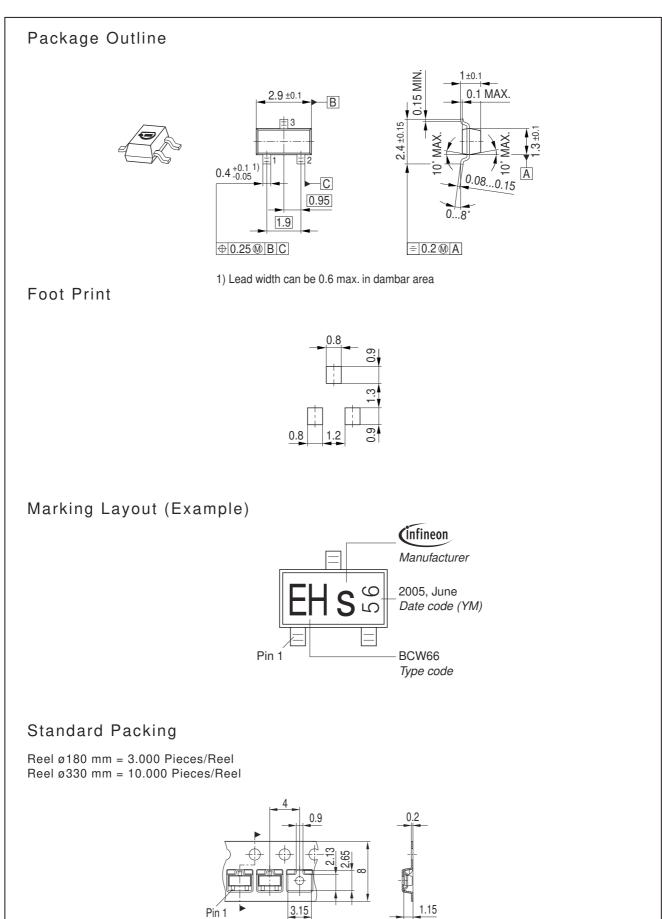




Forward current $I_{\rm F} = f(T_{\rm S})$









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